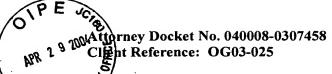
PATENT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

JIN HYO JUNG

Application No.:

10/747,619

Confirmation

4031

No:

Filed:

December 30, 2003

Group No.:

2818 Unassigned

Examiner
For: METHOD FOR FABRICATING FLASH MEMORY DEVICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

APPLICATION DATA SHEET 37 C.F.R. § 1.76

BIBLIOGRAPHIC DATA

1. Applicant information

First applicant: JIN HYO JUNG Citizenship: Republic of Korea

Residence: Anam Semiconductor Inc., Bucheon Plant, Dodang-dong, Wonmi-gu,

Bucheon-si, Gyeonggi-do, 420-712, Republic of Korea

2. Correspondence information

Correspondence for this application should be addressed as follows:

Customer No.: 00909

3. Application information

Title of Invention: METHOD FOR FABRICATING FLASH MEMORY DEVICE

Docket number assigned to this application: 040008-0307458

Suggested Classification: Class:

Cub dasa

Subclass:

Technology Center to which subject matter is assigned:

Total number of drawing sheets: 4

Type of application: Utility

Application is to be published. Suggested drawing figure for publication: Figure 2A

Secrecy order under § 5.2:

This application subject matter of an application which is under a secrecy order pursuant to § 5.2.

4. Representative information

The following have a power of attorney or authorization of agent in this application:

Customer No.: 00909

5. Foreign priority information

Foreign priority is claimed for this application as follows:

Country: Republic of Korea

Application No.: 10-2003-0069217 Filing Date: October 6, 2003

Status: Pending

6. Assignee information

The assignee(s) of this application is/are:

Anam Semiconductor, Inc.
891-10 Daechi -dong, Gangnam-gu
Seoul, 135-523
Republic of Korea
Extent of interest of assignee in application: Entire

Date: April 29, 2004

Pillsbury Winthrop LLP P.O. Box 10500 McLean, VA 22102 Customer No. 00909 Signature of Practitioner

Glenn T. Barrett

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703-(905) 2011